

1 **ABSTRACT OF THE INVENTION**

2 The invention relates to a phase-change memory device. The device includes a double-
3 wide trench into which a single film is deposited but two isolated lower electrodes are formed
4 therefrom. Additionally a diode stack is formed that communicates to the lower electrode.
5 Additionally, other isolated lower electrodes may be formed along a symmetry line that is
6 orthogonal to the first two isolated lower electrodes. The present invention also relates to a
7 method of making a phase-change memory device. The method includes forming two
8 orthogonal and intersecting isolation structures around a memory cell structure diode stack.

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